

SN74HCT595-Q1 車載用、3 ステート出力レジスタ付き 8 ビット シフト・レジスタ

1 特長

- 車載アプリケーション用に AEC-Q100 認定取得済み：
 - デバイス温度グレード 1：
 - 40°C ~ +125°C, T_A
 - デバイス HBM ESD 分類レベル 2
 - デバイス CDM ESD 分類レベル C6
- LSTTL 入力ロジック互換
 - V_{IL(max)} = 0.8V, V_{IH(min)} = 2V
- CMOS 入力ロジック互換
 - I_I ≤ 1μA (V_{OL}, V_{OH})
- 4.5V ~ 5.5V で動作
- 最大 10 個の LSTTL 負荷ファンアウトに対応
- シフト・レジスタはダイレクト・クリアを装備

2 アプリケーション

- 出力拡張
- LED マトリクス制御
- 7 セグメント・ディスプレイ制御
- 8 ビット・データ・ストレージ

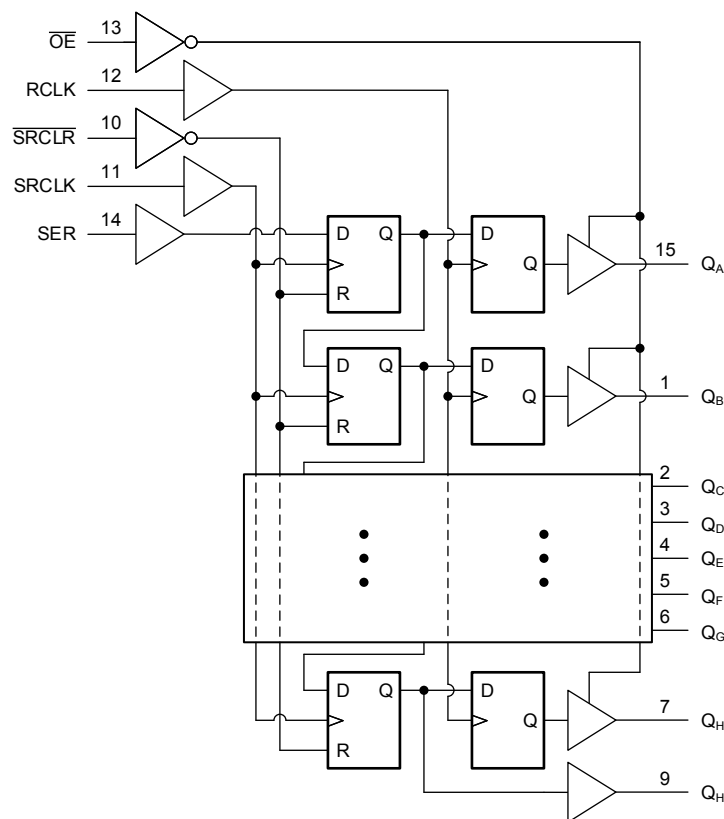
3 概要

SN74HCT595-Q1 デバイスには 8 ビットのシリアル・イン、パラレル・アウトのシフト・レジスタが搭載されており、8 ビットの D タイプ・ストレージ・レジスタへデータを供給します。ストレージ・レジスタはパラレルの 3 ステート出力を備えています。シフト・レジスタとストレージ・レジスタの両方に、それぞれ独立したクロックが供給されます。シフト・レジスタはダイレクト・オーバーライディング・クリア (SRCLR) 入力、シリアル (SER) 入力、カスケード用シリアル出力 (Q_H) を備えています。出力イネーブル (OE) 入力が High のとき、出力は高インピーダンス状態になります。内部レジスタ・データおよびシリアル出力 (Q_H) は、OE 入力の動作による影響を受けません。

製品情報⁽¹⁾

部品番号	パッケージ	本体サイズ (公称)
SN74HCT595PW-Q1	TSSOP (16)	5.00mm × 4.40mm

(1) 利用可能なすべてのパッケージについては、このデータシート末尾にある注文情報を参照してください。



論理図 (正論理)



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4 Revision History

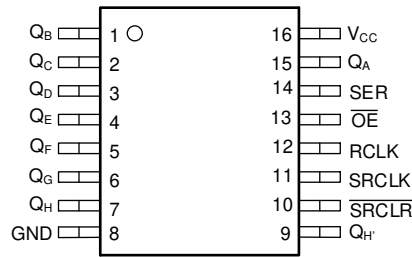
資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (October 2021) to Revision A (December 2021)

Page

• データシートのステータスを事前情報から <i>量産データ</i> に更新	1
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5 Pin Configuration and Functions



**图 5-1. PW Package
16-Pin TSSOP
Top View**

表 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
Q _B	1	O	Q _B O
Q _C	2	O	Q _C O
Q _D	3	O	Q _D O
Q _E	4	O	Q _E O
Q _F	5	O	Q _F O
Q _G	6	O	Q _G O
Q _H	7	O	Q _H O
GND	8	—	Ground
Q _H	9	O	Serial O, can be used for cascading
$\overline{\text{SRCLR}}$	10	I	Shift register clear, active low
SRCLK	11	I	Shift register clock, rising edge triggered
RCLK	12	I	O register clock, rising edge triggered
$\overline{\text{OE}}$	13	I	O Enable, active low
SER	14	I	Serial I
Q _A	15	O	Q _A O
V _{CC}	16	—	Positive supply

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	-0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	V _I < 0 or V _I > V _{CC} + 0.5 V		mA
I _{OK}	Output clamp current ⁽²⁾	V _O < 0 or V _O > V _{CC} + 0.5 V		mA
I _O	Continuous output current	V _O = 0 to V _{CC}		mA
I _{CC}	Continuous output current through V _{CC} or GND	-70	70	mA
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature	-65	150	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level 2	±4000
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1500

- (1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	4.5	5	5.5	V
V _{IH}	High-level input voltage	V _{CC} = 4.5 V to 5.5V		2	V
V _{IL}	Low-level input voltage	V _{CC} = 4.5 V to 5.5V		0.8	V
V _I	Input voltage	0		V _{CC}	V
V _O	Output voltage	0		V _{CC}	V
Δt/Δv	Input transition rise and fall rate	V _{CC} = 4.5 V to 5.5V		500	ns/V
T _A	Ambient temperature	-40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74HCT595-Q1	UNIT
		PW (TSSOP)	
		16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	131.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	69.8	°C/W
R _{θJB}	Junction-to-board thermal resistance	76.5	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	20.9	°C/W
Y _{JB}	Junction-to-board characterization parameter	76.1	°C/W

6.4 Thermal Information (continued)

THERMAL METRIC ⁽¹⁾		SN74HCT595-Q1		
		PW (TSSOP)		
		16 PINS		
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A		°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A = 25^\circ\text{C}$			$-40^\circ\text{C to } 125^\circ\text{C}$			UNIT	
		MIN	TYP	MAX	MIN	TYP	MAX		
V_{OH}	High-level output voltage $V_I = V_{IH}$ or V_{IL}	$I_{OH} = -20 \mu\text{A}, V_{CC} = 4.5 \text{ V}$	4.4			4.4			V
		$I_{OH} = -6 \text{ mA}, V_{CC} = 4.5 \text{ V}$	3.98			3.84			V
V_{OL}	Low-level output voltage $V_I = V_{IH}$ or V_{IL}	$I_{OL} = 20 \mu\text{A}, V_{CC} = 4.5 \text{ V}$				0.1			V
		$I_{OL} = 6 \text{ mA}, V_{CC} = 4.5 \text{ V}$				0.33			V
I_I	Input leakage current $V_I = V_{CC}$ or 0	$V_{CC} = 5.5 \text{ V}$				± 100			nA
I_{OZ}	Off-State (High-Impedance State) Output Current $V_O = V_{CC}$ or 0, Q_A^- , Q_H	$V_{CC} = 5.5 \text{ V}$				± 0.5			μA
I_{CC}	Supply current $V_I = V_{CC}$ or 0, $I_O = 0$	$V_{CC} = 5.5 \text{ V}$	8			80			μA
ΔI_{CC}	Additional Quiescent Device Current Per Input Pin $V_I = V_{CC} - 2.1 \text{ V}$ $V_I = 0.5 \text{ V}$ or 2.4 V	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	126.2			157.5			μA
		$V_{CC} = 5.5 \text{ V}$	2.4			2.9			mA
C_i	Input capacitance $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	10						pF
C_O	Output capacitance $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	20						pF
C_{pd}	Power dissipation capacitance per gate No load		50						pF

6.6 Timing Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	CONDITION	V_{CC}	$T_A = 25^\circ\text{C}$		$-40^\circ\text{C to } 125^\circ\text{C}$		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	4.5 V	31		25		MHz
t_w	Pulse duration	SRCLK or RCLK high or low	4.5 V	16	20		ns
			5.5 V	16	20		
		SRCLR low	4.5 V	16	20		
			5.5 V	16	20		

6.6 Timing Characteristics (continued)

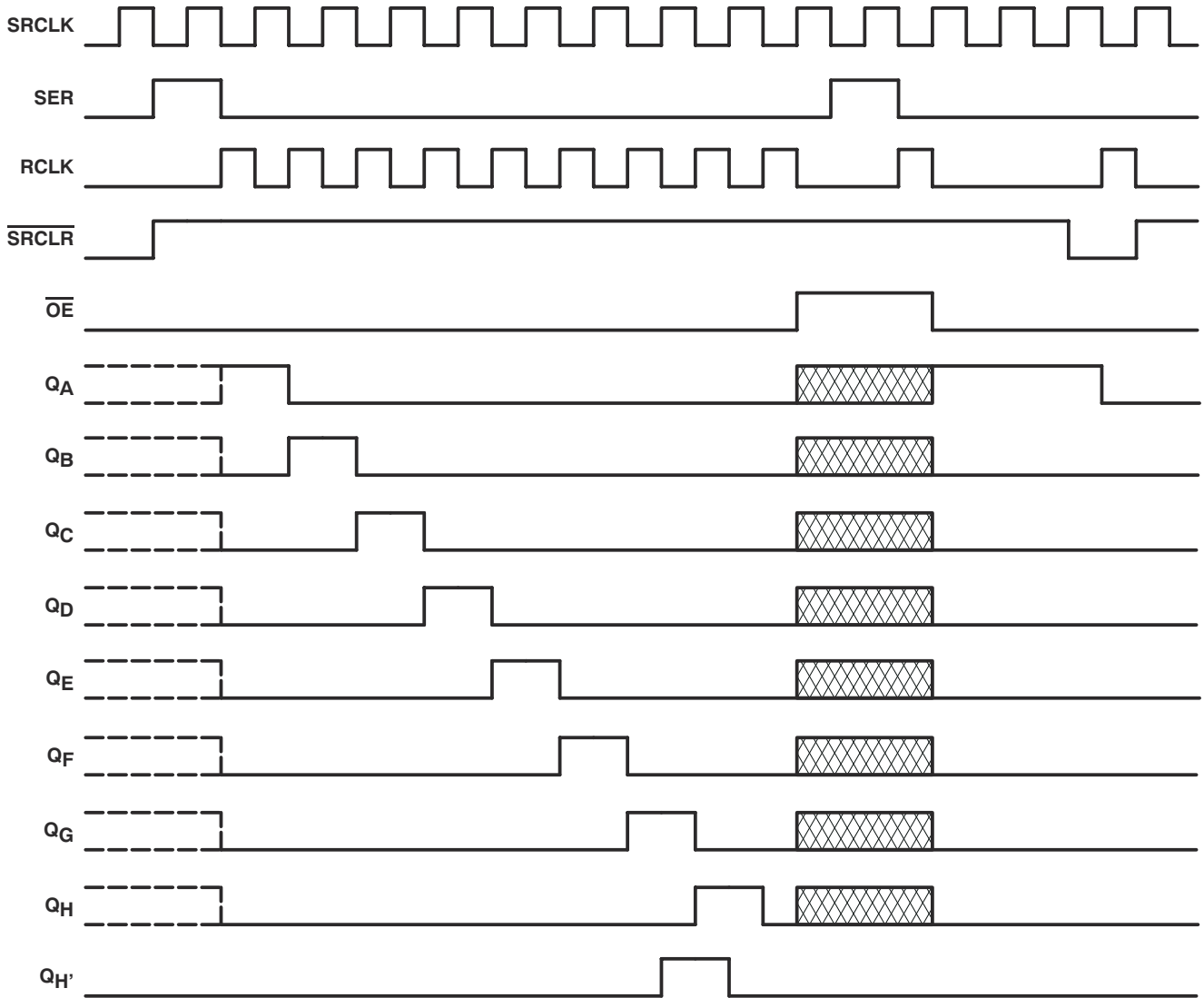
over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	CONDITION	V _{CC}	T _A = 25°C		-40°C to 125°C		UNIT
			MIN	MAX	MIN	MAX	
t _{su}	SER before SRCLK↑	4.5 V	20		25	ns	
		5.5 V	20		25		
	SRCLK↑ before RCLK↑	4.5 V	16		20		
		5.5 V	16		20		
	SRCLR low before RCLK↑	4.5 V	10		13		
		5.5 V	10		13		
SRCLR high (inactive) before SRCLK↑	4.5 V	10		12			
	5.5 V	10		12			
t _h	Hold time	4.5 V	0		0	ns	
		5.5 V	0		0		

6.7 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	T _A = 25°C			-40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
f _{max}			4.5 V	31			25			MHz
t _{pd}	Propogation delay	SRCLK	Q _{H'}	4.5 V		42			53	ns
				5.5 V		42			53	
	RCLK	Q _A - Q _H	4.5 V		40			50		
			5.5 V		40			50		
t _{PHL}	Propogation delay	SRCLR	Q _{H'}	4.5 V		40			50	ns
				5.5 V		40			50	
t _{en}	Enable time	OE	Q _A - Q _H	4.5 V		35			44	ns
				5.5 V		35			44	
t _{dis}	Disable time	OE	Q _A - Q _H	4.5 V		30			38	ns
				5.5 V		30			38	
t _t	Transition-time		Any output	4.5 V		12			15	ns
			Any output	5.5 V		14			17	



NOTE:  implies that the output is in 3-State mode.

6-1. Timing Diagram

6.8 Typical Characteristics

$T_A = 25^\circ\text{C}$

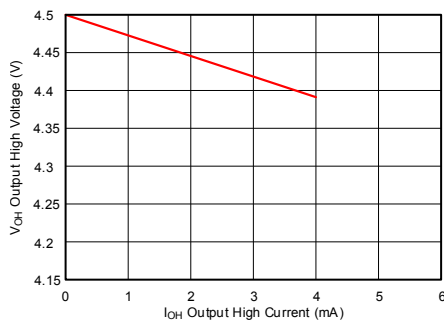


Figure 6-2. Typical Output Voltage in the High State (V_{OH})

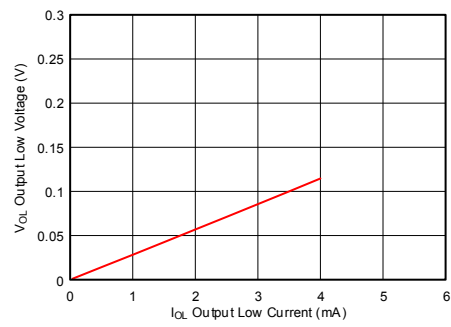


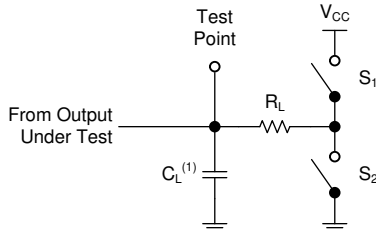
Figure 6-3. Typical Output Voltage in the Low State (V_{OL})

7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_O = 50 \Omega$, $t_t < 6 \text{ ns}$.

For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



(1) C_L includes probe and test-fixture capacitance.

FIG 7-1. Load Circuit for 3-State Outputs

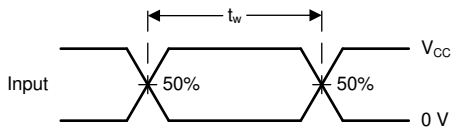
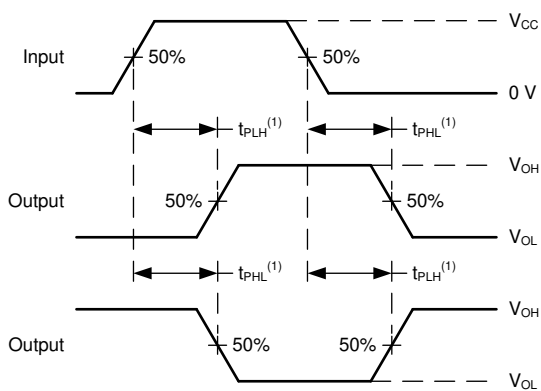
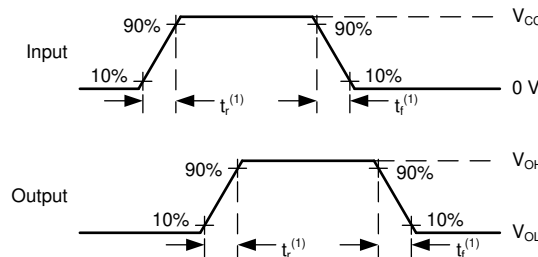


FIG 7-3. Voltage Waveforms, Pulse Duration



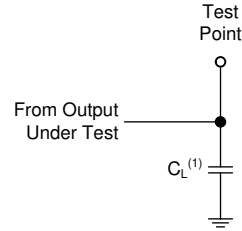
(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .

FIG 7-5. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t .

FIG 7-7. Voltage Waveforms, Input and Output Transition Times



(1) C_L includes probe and test-fixture capacitance.

FIG 7-2. Load Circuit for Push-Pull Outputs

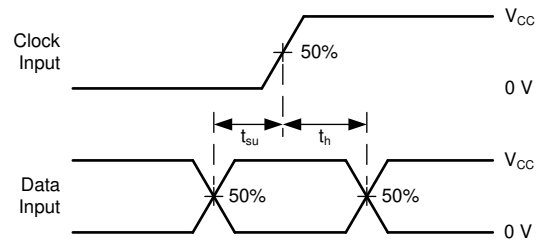


FIG 7-4. Voltage Waveforms, Setup and Hold Times

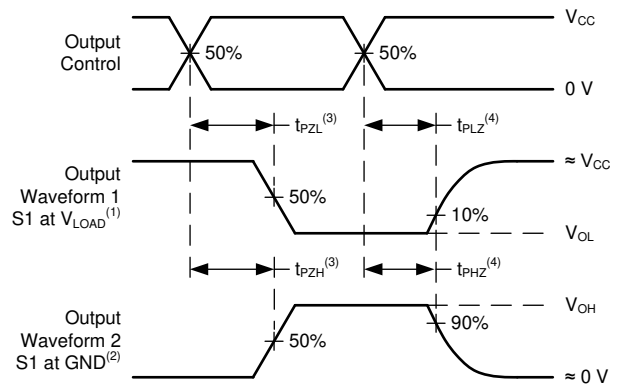


FIG 7-6. Voltage Waveforms Propagation Delays

8 Detailed Description

8.1 Functional Block Diagram

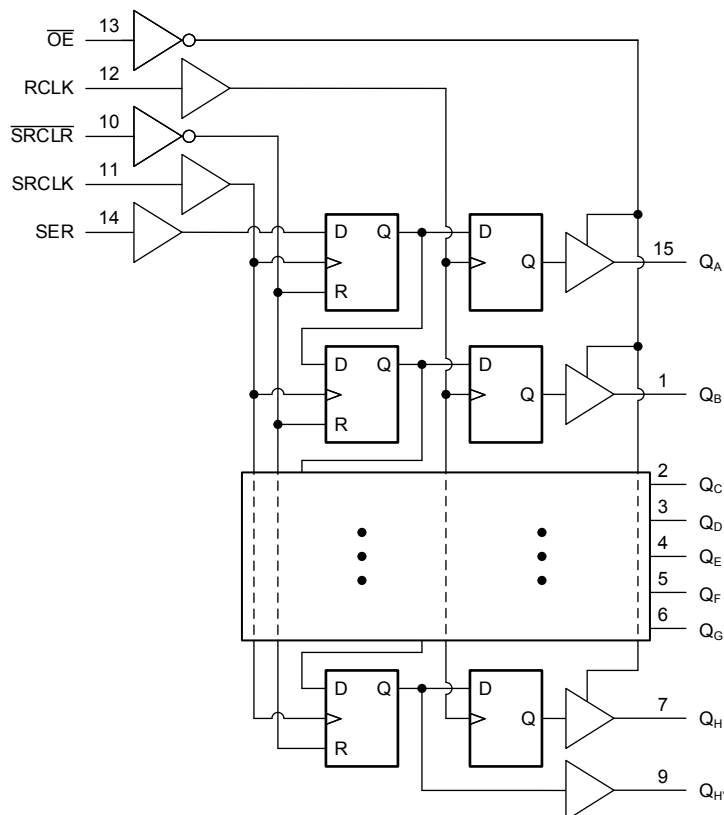


图 8-1. Logic Diagram (Positive Logic) for the SN74HCT595-Q1

8.2 Feature Description

8.2.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-State outputs. The three states that these outputs can be in are driving high, driving low, and high impedance. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10 kΩ resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

8.2.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.2.3 TTL-Compatible CMOS Inputs

This device includes TTL-compatible CMOS inputs. These inputs are specifically designed to interface with TTL logic devices by having a reduced input voltage threshold.

TTL-compatible CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ($R = V \div I$).

TTL-compatible CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the [Implications of Slow or Floating CMOS Inputs](#) application report.

Do not leave TTL-compatible CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10-k Ω resistor is recommended and will typically meet all requirements.

8.2.4 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

8.2.5 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in [Figure 8-2](#).

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

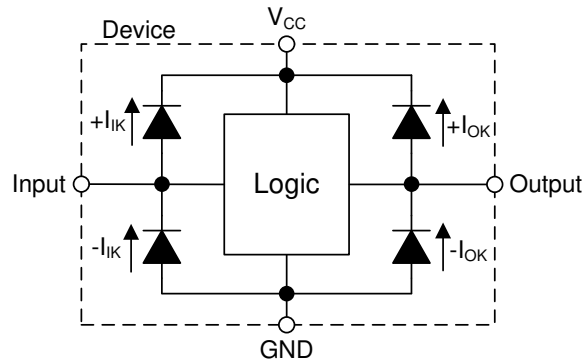


图 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.3 Device Functional Modes

Function Table lists the functional modes of the SN74HCT595-Q1.

表 8-1. Function Table

INPUTS					FUNCTION
SER	SRCLK	SRCLR	RCLK	OE	
X	X	X	X	H	Outputs Q _A – Q _H are disabled
X	X	X	X	L	Outputs Q _A – Q _H are enabled.
X	X	L	X	X	Shift register is cleared.
L	↑	H	X	X	First stage of the shift register goes low. Other stages store the data of previous stage, respectively.
H	↑	H	X	X	First stage of the shift register goes high. Other stages store the data of previous stage, respectively.
X	X	H	↑	X	Shift-register data is stored in the storage register.
X	↑	H	↑	X	Data in shift register is stored in the storage register, the data is then shifted through.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

In this application, the SN74HCT595-Q1 is used to control seven-segment displays. Utilizing the serial output and combining a few of the input signals, this implementation reduces the number of I/O pins required to control the displays from sixteen to four. Unlike other I/O expanders, the SN74HCT595-Q1 does not need a communication interface for control. It can be easily operated with simple GPIO pins.

The OE pin is used to easily disable the outputs when the displays need to be turned off or connected to a PWM signal to control brightness. However, this pin can be tied low and the outputs of the SN74HCT595-Q1 can be controlled accordingly to turn off all the outputs reducing the I/O needed to three. There is no practical limitation to how many SN74HCT595-Q1 devices can be cascaded. To add more, the serial output will need to be connected to the following serial input and the clocks will need to be connected accordingly. With separate control for the shift registers and output registers, the desired digit can be displayed while the data for the next digit is loaded into the shift register.

At power-up, the initial state of the shift registers and output registers are unknown. To give them a defined state, the shift register needs to be cleared and then clocked into the output register.

9.2 Typical Application

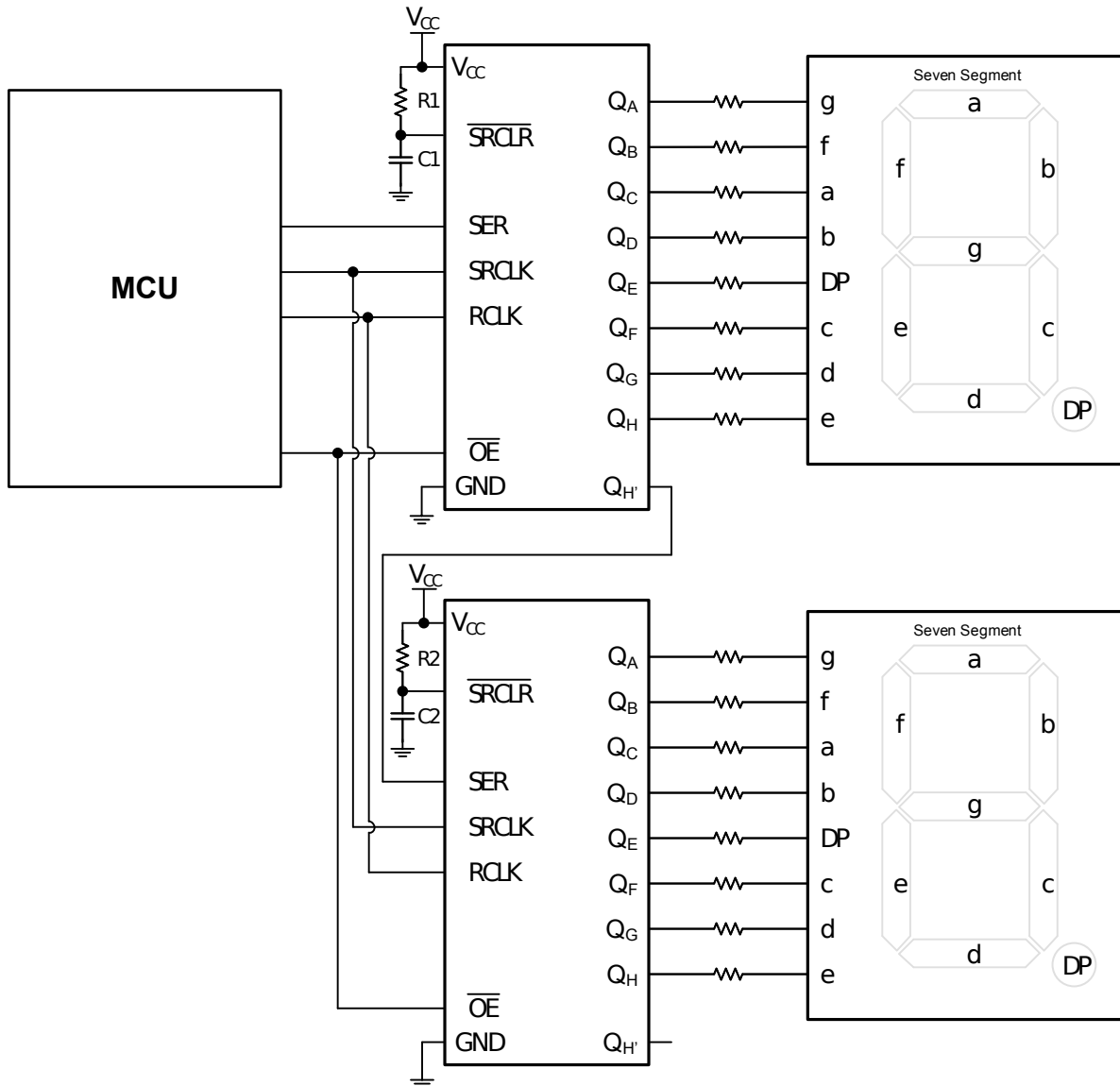


图 9-1. Typical Application Block Diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCT595-Q1 plus the maximum static supply current, I_{CC} , listed in *Electrical Characteristics* and any transient current required for switching. The logic device can only source as much current as is provided by the positive supply source. Be sure not to exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCT595-Q1 plus the maximum supply current, I_{CC} , listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HCT595-Q1 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74HCT595-Q1 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the high state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCT595-Q1, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The SN74HCT595-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to *Feature Description* section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCT595-Q1 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

9.2.3 Application Curve

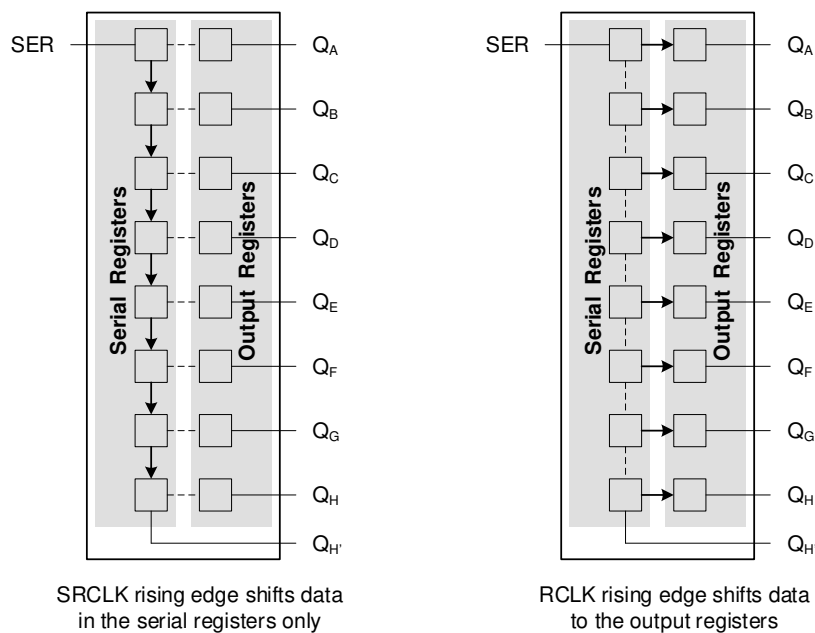


Figure 9-2. Simplified Functional Diagram Showing Clock Operation

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μF and 1- μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

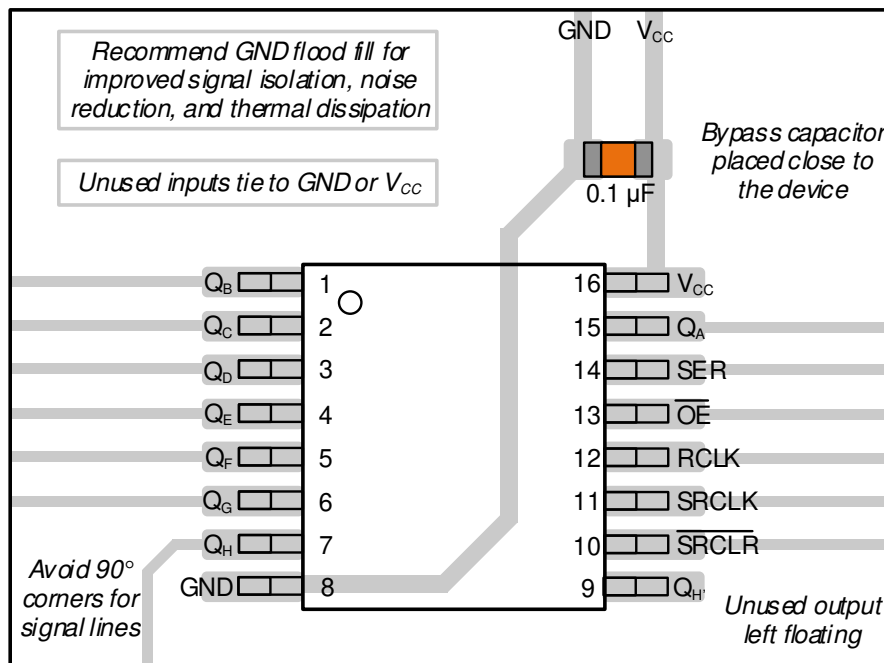


图 11-1. Example Layout for the SN74HCT595-Q1

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [HCMOS Design Considerations application report](#)
- Texas Instruments, [CMOS Power Consumption and \$C_{pd}\$ Calculation application report](#)
- Texas Instruments, [Designing With Logic application report](#)

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 サポート・リソース

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12.4 Trademarks

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74HCT595QPWRQ1	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HT595Q
SN74HCT595QPWRQ1.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HT595Q

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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OTHER QUALIFIED VERSIONS OF SN74HCT595-Q1 :

- Catalog : [SN74HCT595](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCT595QPWRQ1	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCT595QPWRQ1	TSSOP	PW	16	2000	356.0	356.0	35.0



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NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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